

METHOD OF FORMING A MATERIAL LAYER IN A SEMICONDUCTOR STRUCTURE**ABSTRACT**

A method comprises depositing a first portion (105) of a first material layer (117, 217) on a semiconductor structure (100, 200). A first run (108) of a post-treatment process is performed for modifying at least the first portion (105) of the first material layer (117, 217). After the first run of the post-treatment process, a second portion (109) of the first material layer is deposited. The second portion (109) is formed of substantially the same material as the first portion (105). After the deposition of the second portion of the first material layer, a second run (111) of the post-treatment process is performed for modifying at least the second portion (109) of the first material layer (117, 217).

FIG. 1e